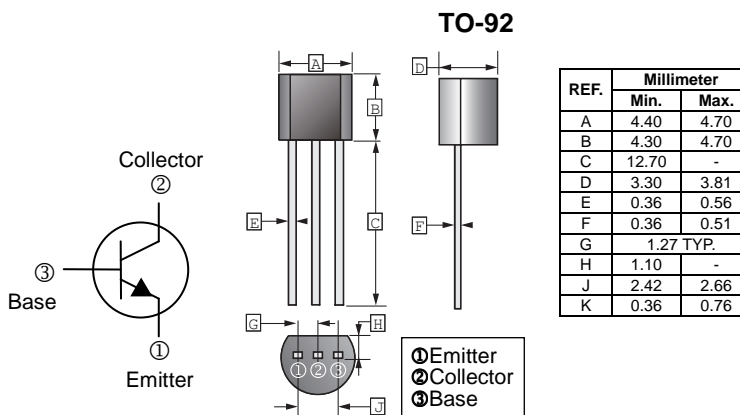


RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- Power switching applications



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V _{CB0}	600	V
Collector to Emitter Voltage	V _{CEO}	500	V
Emitter to Base Voltage	V _{EBO}	6	V
Collector Current - Continuous	I _C	0.8	A
Collector Power Dissipation	P _C	800	mW
Thermal Resistance from Junction to Ambient	R _{θJA}	156	°C / W
Junction and Storage Temperature	T _J , T _{STG}	150, -55~150	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Collector to Base Breakdown Voltage	V _{(BR)CBO}	600	-	-	V	I _C =100μA, I _E =0
Collector to Emitter Breakdown Voltage	V _{(BR)CEO}	500	-	-	V	I _C =1mA, I _B =0
Emitter to Base Breakdown Voltage	V _{(BR)EBO}	6	-	-	V	I _E =100μA, I _C =0
Collector Cut – Off Current	I _{CBO}	-	-	100	μA	V _{CB} =600V, I _E =0
	I _{CEO}	-	-	100		V _{CE} =500V, I _B =0
Emitter Cut – Off Current	I _{EBO}	-	-	100	μA	V _{EB} =6V, I _C =0
DC Current Gain	h _{FE}	20	-	30		V _{CE} =10V, I _C =200mA
		5	-	-		V _{CE} =10V, I _C =0.25mA
Collector to Emitter Saturation Voltage	V _{CE(sat)}	-	-	0.5	V	I _C =200mA, I _B =40mA
Base to Emitter Saturation Voltage	V _{BE(sat)}	-	-	1.1	V	I _C =200mA, I _B =40mA
Transition Frequency	f _T	-	5	-	MHz	V _{CE} =10V, I _C =100mA, f =1MHz
Storage time	t _S	-	2.5	-	μS	I _{B1} = -I _{B2} =0.2A, I _C =1A, V _{CC} =100V
Fall time	t _F	-	0.5	-		

CHARACTERISTIC CURVES

Static Characteristic

